

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	1.4533	N/A	2.2103
RT2	17.3894	N/A	1.8456
RT3	53.4932	N/A	9.5636
RT4	7.6641	N/A	2.3805
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	21.3508 m	N/A	31.0748 m
CT2	41.0128 m	N/A	128.7508 m
CT3	1.4298	N/A	150.3429 m
CT4	491.3727 m	N/A	25.2299 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	2.3339	N/A	575.5312 m
RF2	17.8843	N/A	6.8042
RF3	11.5786	N/A	8.4874
RF4	48.2032	N/A	132.8688 m
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	8.7151 m	N/A	5.8049 m
CF2	25.2051 m	N/A	8.4331 m
CF3	266.7055 m	N/A	146.8477 m
CF4	1.2849	N/A	2.2433 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

